

Xiang Xiao

List of Publications by Year in descending order

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24
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518
citing authors

#	ARTICLE	IF	CITATIONS
1	Room-Temperature-Processed Flexible Amorphous InGaZnO Thin Film Transistor. ACS Applied Materials & Interfaces, 2018, 10, 25850-25857.	8.0	36
2	Photoreactive and Metal-Platable Copolymer Inks for High-Throughput, Room-Temperature Printing of Flexible Metal Electrodes for Thin-Film Electronics. Advanced Materials, 2016, 28, 4926-4934.	21.0	77
3	Indium-Tin-Oxide Thin-Film Transistors With In Situ Anodized Ta ₂ O ₅ Passivation Layer. IEEE Electron Device Letters, 2016, 37, 603-606.	3.9	12
4	A Back-Channel-Etched Amorphous InGaZnO Thin-Film Transistor Technology With Al-Doped ZnO as Source/Drain and Pixel Electrodes. IEEE Transactions on Electron Devices, 2016, 63, 2205-2209.	3.0	15
5	Comparison of N ₂ and Ar plasma treatment for source/drain formation in self-aligned top-gate amorphous InGaZnO thin film transistor. , 2016, , .		1
6	Oxygen partial pressure and annealing temperature influence on the performance of back-channel-etch zinc tin oxide thin film transistors. , 2016, , .		1
7	Estimation of threshold voltage shift in a-IGZO TFTs under different bias temperature stress by improved stretched-exponential equation. , 2016, , .		3
8	Impact of wet etchant with different PH value on the performance of back-channel-etch a-IGZO thin-film-transistor. , 2016, , .		0
9	Characteristics of amorphous In-Ga-Zn-O thin-film-transistors with channel layer deposited by bias sputtering. , 2016, , .		0
10	Improved Electrical Stability of Double-Gate a-IGZO TFTs. Digest of Technical Papers SID International Symposium, 2015, 46, 1151-1154.	0.3	5
11	Comparative study of a-IGZO TFTs with direct current and radio frequency sputtered channel layers. Journal of the Society for Information Display, 2015, 23, 306-312.	2.1	3
12	Back Channel Anodization Amorphous Indium Gallium Zinc Oxide Thin-Film Transistors Process. IEEE Electron Device Letters, 2015, 36, 357-359.	3.9	9
13	Low-Voltage a-InGaZnO Thin-Film Transistors With Anodized Thin HfO ₂ Gate Dielectric. IEEE Electron Device Letters, 2015, 36, 573-575.	3.9	51
14	Effects of over-etching time on the characteristics of amorphous IGZO thin-film transistors with back-channel-etch structure. , 2015, , .		2
15	Fabrication of p-type copper oxide thin-film transistors at different oxygen partial pressure. , 2014, , .		6
16	Characteristics of double-gate a-IGZO TFT. , 2014, , .		2
17	Indium gallium zinc oxide - Carbon nanotube composite thin film transistor. , 2014, , .		1
18	A Multi-V _{th} a-IGZO TFT Technology Using Anodization to Selectively Reduce Oxygen Vacancy Concentration in Channel Regions. IEEE Electron Device Letters, 2014, 35, 1248-1250.	3.9	3

#	ARTICLE	IF	CITATIONS
19	Anodized ITO Thin-Film Transistors. <i>Advanced Functional Materials</i> , 2014, 24, 4170-4175.	14.9	41
20	Study on the transition between p and n types of SnO _x film deposited by DC sputtering. , 2014, , .		1
21	Homojunction In ₂ O ₃ -TFTs prepared by anodization technique. , 2014, , .		0
22	Fabrication of indium-tin-oxide thin-film transistor using anodization. , 2014, , .		0
23	Impacts of substrate heating schemes on characteristics of amorphous indium-gallium-zinc-oxide (a-IGZO) TFTs fabricated on flexible substrates. , 2014, , .		1
24	a-IGZO TFTs With Inductively Coupled Plasma Chemical Vapor Deposited SiO_x Gate Dielectric. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 2687-2690.	3.0	10